

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. DLED.004CP1C1	APPLICATION NO. 10/689,544
INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Vasily I. Shveykin	GROUP 2842- 2826
		FILING DATE October 20, 2003	

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
MLT	1	4,063,189	12/13/77	Scifres et al.			
	2	5,101,413	3/31/92	Botez			
	3	5,537,433	7/16/96	Watanabe			
	4	5,705,834	1/1998	Egalon et al.			
	5	5,779,924	7/1998	Krames et al.			
	6	5,793,062	8/1998	Kish, Jr. et al.			
	7	5,818,860	10/1998	Garbuzov			
	8	6,057,562	5/2000	Lee et al.			
	9	6,429,462	8/2002	Shveykin			
MLT	10	6,649,938	11/2003	Bogatov et al.			

## FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
MLT	11	SU 1329533 A1	05/1998	Soviet Union			X	
	12	SU 1359833 A1	15/12/87	Soviet Union			X	
	13	1,455,373	30/01/89	Soviet Union				
	14	2,133,534	7/20/99	Russia				
	15	2,134,007	07/27/99	Russia			X	
	16	2,142,661	12/10/99	Russia			X	
	17	2,142,665	12/10/99	Russia			X	
	18	EP 0 247 267 B1	10/1991	Europe				
	19	EP 0727827 A3	21/08/96	Europe				
	20	EP 0849812 A3	24/06/98	Europe				
	21	60-211993	10/1985	Japan				
	22	WO 85/03809 A1	29/08/85	WIPO				
	23	WO 99/46838	09/1999	WIPO			X	
MLT	24	WO 99/08352	02/1999	WIPO				

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\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 608; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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FOREIGN PATENT DOCUMENTS								
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							YES	NO
MLT	25	WO 00/10235	02/2000	WIPO			X	
MLT	26	WO 00/39860	07/2000	WIPO			X	

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
MLT	27	<i>High-Efficiency InGaAlP Visible Light-Emitting Diodes</i> , H. Sugawara et al., <i>Japanese Journal of Applied Physics</i> , Vol. 31, No. 8, August 1992, pp. 2446-2451.
	28	<i>Room-Temperature CW Operation of InGaAsP Lasers on Si Fabricated by Wafer Bonding</i> , H. Wada et al., <i>IEEE Photonics Technology Letters</i> , Vol. 8, No. 2, February 1996, pp. 173-175.
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	31	<i>Thin-Films Field-Transfer Matrix Theory of Planar Multilayer Waveguides and Reflection From Prism-Loaded Waveguides</i> , J. Chilwell et al., <i>Journal of the Optical Society of America</i> , Vol. 1, No. 7, July 1984, pp. 742-753.
	32	<i>Wide Spectrum Single Quantum Well Superluminescent Diodes At 0.8 μm With Bent Optical Waveguide</i> , A. T. Semenov et al., <i>Electronics Letters</i> , Vol. 29, No. 10, May 13, 1993, pp. 854-855.
	33	<i>Superluminescent Diodes with Bent Waveguide</i> , C.-F. Lin et al., <i>IEEE Photonics Technology Letters</i> , Vol. 8, No. 2, February 1996, pp. 206-208.
	34	<i>Low spectral modulation high-power output from a new AlGaAs superluminescent diode/optical amplifier structure</i> , G. A. Alphonse et al., <i>Applied Physics Letters</i> , Vol. 55, No. 22, November 27, 1989, pp. 2289-2291.
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	36	<i>High-Brightness AlGaInP 573-nm Light-Emitting Diode with a Chirped Multiquantum Barrier</i> , C. S. Chang et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. 34, No. 1, January 1998, pp. 77-83.
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	38	<i>Superbright Green InGaP Single-Quantum-Well-Structure Light-Emitting Diodes</i> , S. Nakamura et al., <i>Japanese Journal of Applied Physics</i> , Vol. 34 (1995) pp. L1332-L1335, Part 2, No. 10B, 15 October 1995.
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	40	<i>Room-Temperature CW Operation of InGaAsP Lasers on Si Fabricated by Wafer Bonding</i> , H. Wada et al., <i>IEEE Photonics Technology Letters</i> , Vol. 8, No. 2, February 1996, pp. 173-175.
	41	<i>Optoelektronika [Optoelectronics]</i> , Yu. R. Nosov, <i>Radio i svyaz</i> , [Radio and Communications], Moscow, Publ. (1989), pp. 136-143.
	42	<i>Light-Emitting Diodes with 17% External Quantum Efficiency at 622 Mb/s for High-Bandwidth Parallel Short-Distance Optical Interconnects</i> , R. H. Windisch et al., <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , Vol. 5, No. 2, March/April 1999, pp. 166-171.
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MLT	44	<i>100-mW High-Power Angled-Stripe Superluminescent Diodes with a New Real Refractive-Index-Guided Self-Aligned Structure</i> , T. Takayama et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. 32, No. 11, November 1996, pp. 1981-1987.

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		FILING DATE October 20, 2003	GROUP 2812

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
MLT	45	<i>High-power, high-efficiency 1.3 <math>\mu</math>m superluminescent diodes with a buried bent absorbing guide structure</i> , Haruo Nagai et al., <i>Applied Physics Letters</i> , Volume 54, Number 18, May 1989, pp. 1719-1721.
	46	<i>High power, high efficiency window buried heterostructure GaAlAs superluminescent diode with an integrated absorber</i> , N. S. K. Kwong et al., <i>Applied Physics Letters</i> , Vol. 51, No. 23, December 7, 1987, pp. 1879-1881.
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	48	<i>Measurement of the Modal Reflectivity of an Antireflection Coating on a Superluminescent Diode</i> , I. P. Kaminow et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. QE-19, No. 4, April 1983, pp. 493-495.
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	50	<i>High-Power Near-Diffraction-Limited Tapered Amplifiers at 1064 nm for Optical Intersatellite Communications</i> , P. Chazan et al., <i>IEEE Photonics Technology Letters</i> , Vol. 10, No. 11, November 1998, pp. 1542-1544.
	51	<i>Extremely Low Power Consumption Semiconductor Optical Amplifier Gate for WDM Applications</i> , T. Ito et al., <i>Electronics Letters</i> , Vol. 33, No. 21, October 9, 1997, pp. 1791-1792.
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	53	<i>Wavelength Conversion Using Semiconductor Optical Amplifiers</i> , M. Asghari et al., <i>Journal of Lightwave Technology</i> , Vol. 15, No. 7, July 1997, pp. 1181-1190.
	54	<i>Gain Dynamics of a Saturated Semiconductor Laser Amplifier with 1.47-<math>\mu</math>m LD Pumping</i> , K. Inoue et al., <i>IEEE Photonics Technology Letters</i> , Vol. 8, No. 4, April 1996, pp. 506-508.
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	56	<i>Progress in Long-Wavelength Strained-Layer InGaAs(P) Quantum-Well Semiconductor Laser and Amplifiers</i> , P. J. A. Thijs et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. 30, No. 2, February 1994, pp. 477-499.
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	60	<i>2.0 W CW, Diffraction-Limited Tapered Amplifier with Diode Injection</i> , D. Mehuys et al., <i>Electronics Letters</i> , Vol. 28, No. 21, October 8, 1992, pp. 1944-1946.
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	63	<i>546 km, 140 Mbit/s FSK Coherent Transmission Experiment through 10 Cascaded Semiconductor Laser Amplifiers</i> , S. Ryu et al., <i>Electronics Letters</i> , Vol. 25, No. 25, December 7, 1989, pp. 1682-1684.
	64	<i>Pulse Energy Gain Saturation in Subpico- and Picosecond Pulse Amplification by a Traveling-Wave Semiconductor Laser Amplifier</i> , T. Saitoh et al., <i>IEEE Photonics Technology Letters</i> , Vol. 1, No. 10, October 1989, pp. 297-299.
	65	<i>Polarization-Independent Optical Amplifier with Buried Facets</i> , N. A. Olsson et al., <i>Electronics Letters</i> , Vol. 25, No. 16, August 3, 1989, pp. 1048-1049.
	66	<i>Gain and Noise Characteristics of a 1.5<math>\mu</math>m Near-travelling-wave Semiconductor Laser Amplifier</i> , J.-C. Simon et al., <i>Electronics Letters</i> , Vol. 25, No. 7, March 30, 1989, pp. 434-436.
MLT	67	<i>1.3<math>\mu</math>m Semiconductor Laser Power Amplifier</i> , N. A. Olsson et al., <i>IEEE Photonics Technology Letters</i> , Vol. 1, No. 1, January 1989, pp. 2-3.

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MLT	68	<i>Semiconductor Laser Optical Amplifiers for Use in Future Fiber Systems</i> , M. J. O'Mahony, <i>Journal of Lightwave Technology</i> , Vol. 6, No. 4, April 1988, pp. 531-544.
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	78	<i>Ghost Modes and Resonant Effects in AlGaIn-InGaIn-GaN Lasers</i> , P. G. Eliseev et al., <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , Vol. 5, No. 3, May/June 1999, pp. 771-779.
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	80	<i>High-power (&gt;10 W) continuous-wave operation from 100-<math>\mu</math>m-aperture 0.97-<math>\mu</math>m-emitting Al-free diode lasers</i> , A. Al-Muhanna et al., <i>Applied Physics Letters</i> , Vol. 73, No. 9, August 31, 1998, pp. 1182-1184.
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	86	<i>Aluminum-Free 980-nm GaInAs/GaInAsP/GaInP Pump Lasers</i> , Harry Asonen et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. 30, No. 2, February 1994, pp. 415-423.
	87	<i>600 mW CW Single-Mode GaAlAs Triple-Quantum-Well Laser with a New Index Guided Structure</i> , O. Imafuji et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. 29, No. 6, June 1993, pp. 1889-1894.
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	89	<i>Operating Characteristics of a High-Power Monolithically Integrated Flared Amplifier Master Oscillator Power Amplifier</i> , S. O'Brien et al., <i>IEEE Journal of Quantum Electronics</i> , Vol. 29, No. 6, June 1993, pp. 2052-2057.
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MLT	91	<i>High-Power, Near-Diffraction-Limited Large-Area Traveling-Wave Semiconductor Amplifier</i> , L. Goldberg et al., <u>IEEE Journal of Quantum Electronics</u> , Vol. 29, No. 6, June 1993, pp. 2028-2043.
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	98	<i>Linewidth Broadening Factor in Semiconductor Lasers-An Overview</i> , M. Osinski et al., <u>IEEE Journal of Quantum Electronics</u> , Vol. QE-23, No. 1, January 1987, pp. 9-29.
	99	<i>Nature of Wavelength Chirping in Directly Modulated Semiconductor Lasers</i> , T. L. Koch et al., <u>Electronics Letters</u> , December 6, 1984, Vol. 20, No. 25/26, pp. 1038-1039.
	100	<u>Handbook of Semiconductor Lasers and Photonic Integrated Circuits</u> , Y. Suematsu et al., 1994, pp. 402-407.
	101	<u>Handbook of Semiconductor Lasers and Photonic Integrated Circuits</u> , Y. Suematsu et al., 1994, pp. 44-45, 393-417.
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	105	<i>Analysis of Semiconductor Laser Optical Amplifiers</i> , M. J. Adams et al., <u>IEEE Proceedings</u> , Vol. 132, Pt. J, No. 1, February 1985, pp. 58-63.
	106	<i>Efficiency and intensity distribution of a semiconductor leaky-mode laser</i> , A.P. Bogatov et al., <u>Quantum Electronics</u> , Vol. 26, No. 1, 1999, pp. 28-32. (In Russian)
	107	<i>Directional radiation pattern of quantum-dimensional InGaAs/GaAs leaky-mode lasers</i> , V.I. Shveikin et al., <u>Quantum Electronics</u> , Vol. 26, No. 1, 1999, pp. 33-36. (In Russian)
	108	<i>Dynamics of the optical damage of output mirrors of ridge semiconductor lasers based on strained quantum-well heterostructures</i> , I.V. Akimova et al., <u>Quantum Electronics</u> , Vol. 28, No. 7, 1998, pp. 629-632.
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	113	<i>Improved characteristics of InGaN multiple-quantum-well light-emitting diode by GaN/AlGaN distributed Bragg reflector grown on sapphire</i> , N. Nakada et al., <u>Applied Physics Letters</u> , Vol. 76, No. 14, April 3, 2000, pp. 1804-1806
MLT	114	<i>Room-temperature operation at 333 nm of <math>\text{Al}_{0.63}\text{Ga}_{0.97}\text{N}/\text{Al}_{0.25}\text{Ga}_{0.75}\text{N}</math> quantum-well light-emitting diodes with Mg-doped superlattice layers</i> , A. Kinoshita et al., <u>Applied Physics Letters</u> , Vol. 77, No. 2, July 10, 2000, pp. 175-177

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\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

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	FILING DATE October 20, 2003	GROUP 2812

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
MLT	115	<i>Resonant-cavity InGaN quantum-well blue light-emitting diodes</i> , Y.-K. song et al., <u>Applied Physics Letters</u> , Vol. 77, No. 12, September 18, 2000, pp 1744-1746
MLT	116	<i>Green electroluminescent (Ga, In, Al) N LEDs grown on Si (111)</i> , S. Dalmaso et al., <u>Electronics Letters</u> , Vol. 36, No. 20, September 28, 2000, pp 1728-1730
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MLT	118	<i>Semiconductor Optical Amplifiers</i> , J.-R. Kim et al., <u>Compound Semiconductor</u> , Vol. 6, No. 2, March 2000, pp. 46-48, 50

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